

ABSTRACT OF THE DISCLOSURE

5 A first insulation film is made of a silicon material and is provided on a semiconductor base. A second insulation film is made of an organic material and is provided on the first insulation film. The second insulation film is thicker than the first insulation film. A third insulation film is thinner than the second insulation film and is provided on the second insulation film. The third insulation film is made of a silicon 10 material and has a moisture resistance property. A fourth insulation film is made of an organic material. The fourth insulation film is provided on the third insulation film to prevent a damage on the third insulation film. A wiring layer is provided on the fourth insulation film.